

Product data sheet

# 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

# 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage	-		-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	0.95	Α
Static char	acteristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.9 \text{ A}; T_j = 25 \text{ °C}$		-	211	252	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	654	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$
4	S2	source TR2	☐1 ☐2 ☐3 <b>———</b> —————————————————————————————————	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMGD175XNE	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PMGD175XNE	LU%

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	0.95	Α
		$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C	[1]	-	0.87	Α
		$V_{GS}$ = 4.5 V; $T_{amb}$ = 100 °C	[1]	-	0.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	mW
			[1]	-	310	mW
		T <sub>sp</sub> = 25 °C		-	905	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	390	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode		,	'	'	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.31	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

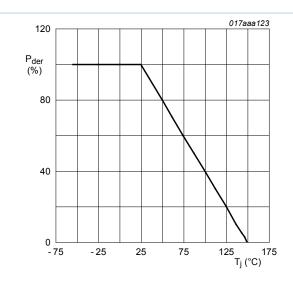


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

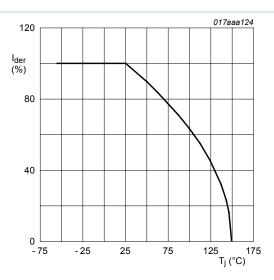


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

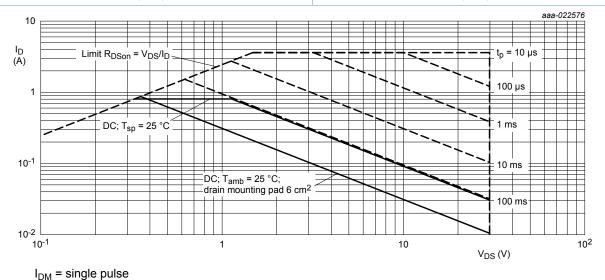


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

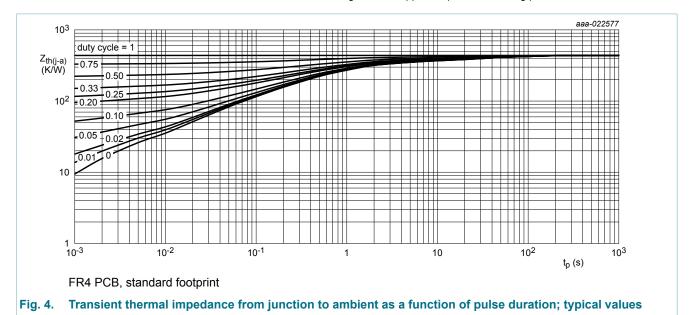
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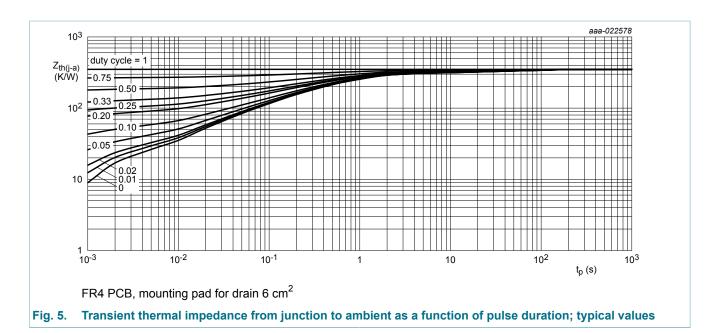
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor									
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	417	480	K/W		
	from junction to ambient		[2]	-	352	405	K/W		
	ambient	in free air; t ≤ 5 s	[2]	-	295	340	K/W		
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	120	138	K/W		
Per device									
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	320	K/W		

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)		l l			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.75	1	1.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C	-	211	252	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 150 °C	-	344	411	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 0.8 A; T <sub>j</sub> = 25 °C	-	267	319	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 0.9 A; $T_j$ = 25 °C	-	3.5	-	S
Dynamic cl	haracteristics (per transist	or)	l l			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 0.9 A; $V_{GS}$ = 4.5 V;	-	1.05	1.65	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.15	-	nC
$Q_{GD}$	gate-drain charge		-	0.27	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	81	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	13	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	9	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $I_D$ = 0.9 A; $V_{GS}$ = 4.5 V;	-	7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	17	-	ns
t <sub>f</sub>	fall time		-	6	-	ns
Source-dra	in diode (per transistor)		ı	1	-	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 0.3 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V

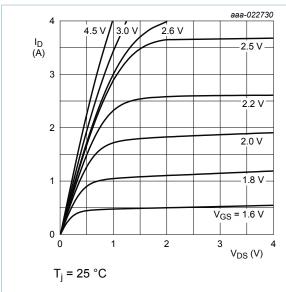


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

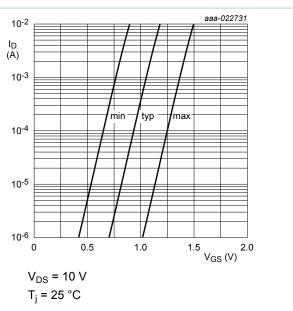


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

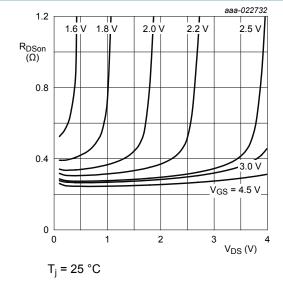


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

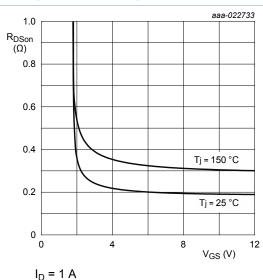


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

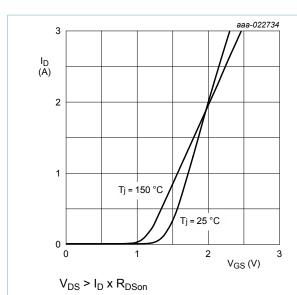


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

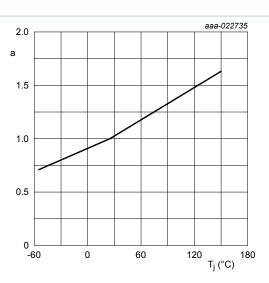


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

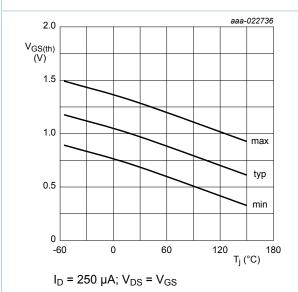


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

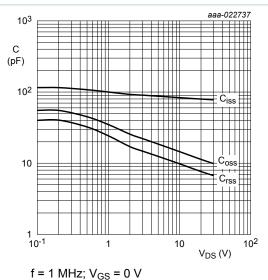


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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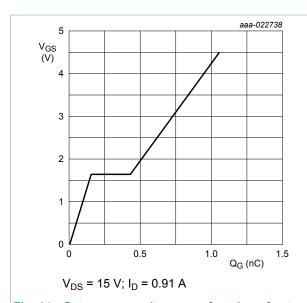


Fig. 14. Gate-source voltage as a function of gate charge; typical values

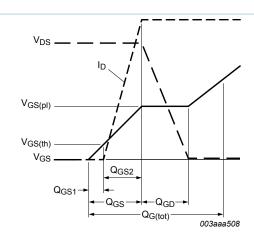


Fig. 15. Gate charge waveform definitions

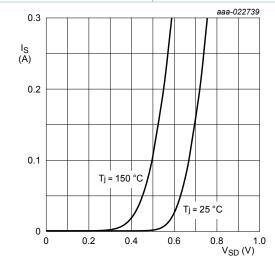
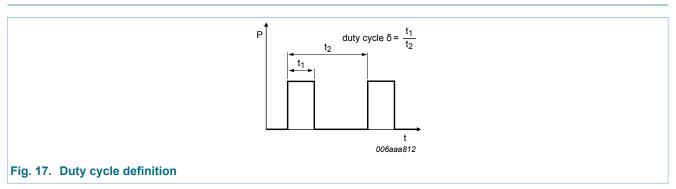


Fig. 16. Source current as a function of source-drain voltage; typical values

# 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

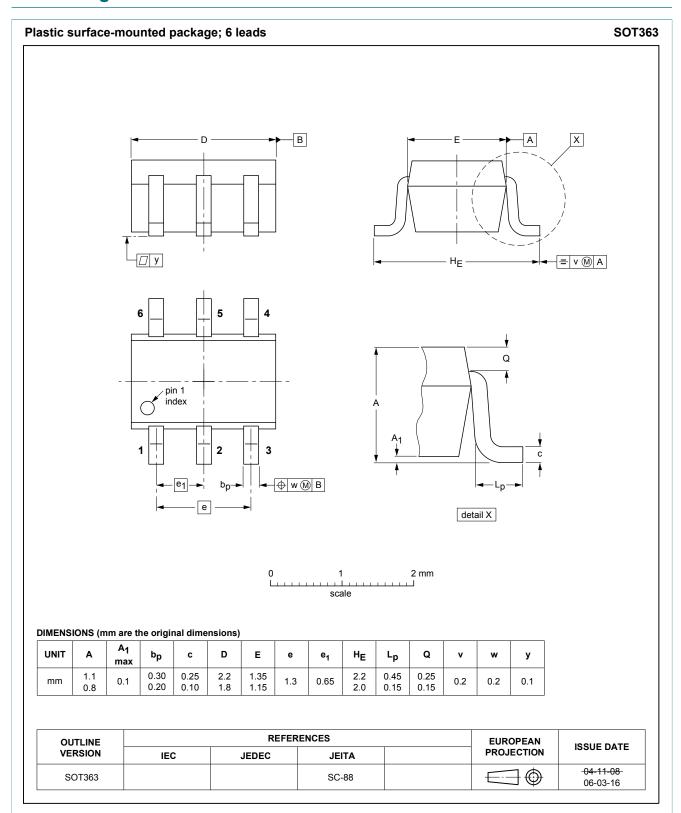


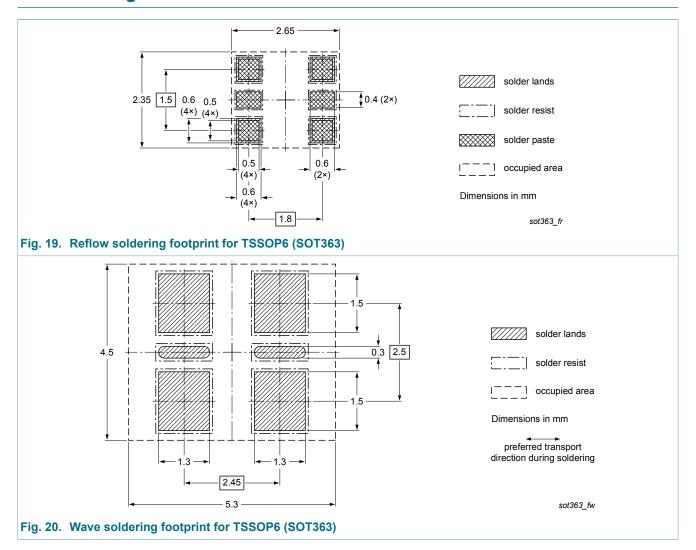
Fig. 18. Package outline TSSOP6 (SOT363)

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# 13. Soldering



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# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMGD175XNE v.1	20160415	Product data sheet	-	-

## 30 V, Dual N-channel Trench MOSFET

# 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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